

N-channel 120 V 7.9 mΩ standard level MOSFET in I2PAK 18 February 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- I2PAK package for slimline adaptors & height constrained applications

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control
- Slimline adaptors & chargers

4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	120	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	349	W
Static chara	cteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	4.7	6.72	7.9	mΩ
Dynamic ch	aracteristics	· · · · · ·	I			
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 60 V;	-	50.5	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15	-	167	-	nC
Avalanche r	ruggedness	· · · · ·	I			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})}\texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D}\texttt{=} 70 \; A; \\ V_{sup} \texttt{\leq} 120 \; V; \; \text{unclamped}; \; R_{GS}\texttt{=} 50 \; \Omega; \\ \hline \textbf{Fig. 3} \end{array}$	-	-	386	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G
mb	D	drain	I2PAK (SOT226)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN7R8-120ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN7R8-120ES	PSMN7R8-120ES

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	120	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	120	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	70	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	70	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	280	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	349	W
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	in diode				
I _S	source current	T _{mb} = 25 °C	-	70	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	280	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^\circC; \; I_D = 70 \; A; \\ V_{sup} \leq 120 \; V; \; unclamped; \; R_{GS} = 50 \; \Omega; \\ \hline Fig. 3 \end{array}$	-	386	mJ

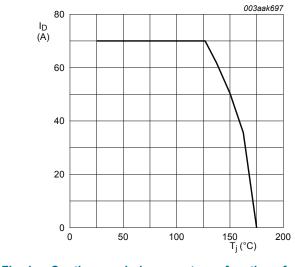


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

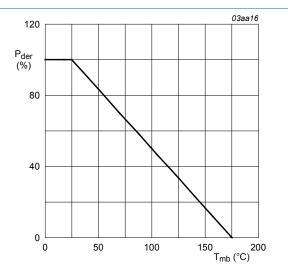
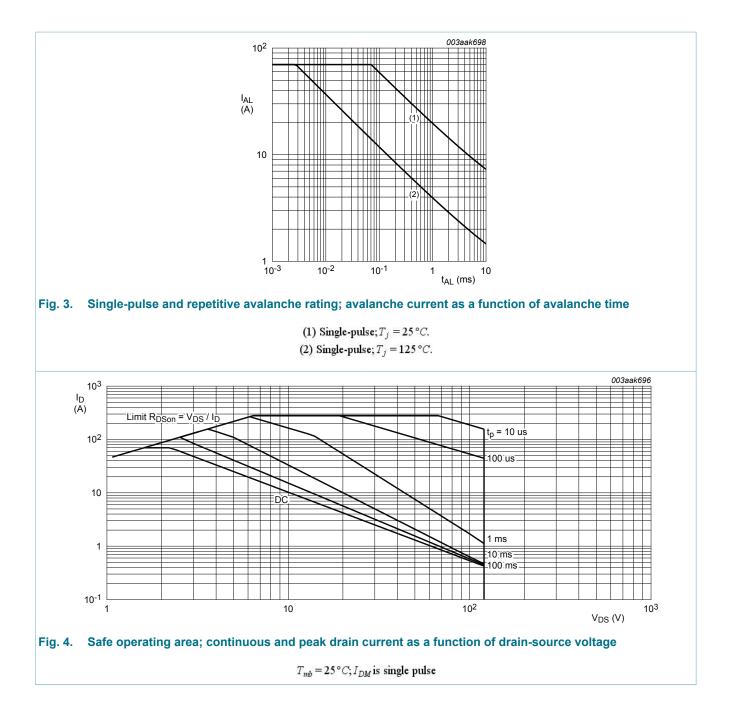


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.35	0.43	K/W

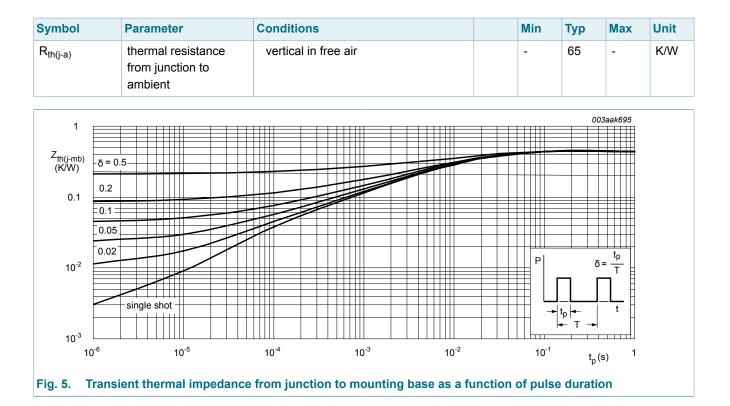
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	120	-	-	V
breakdown vol	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	108	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	2	3	4	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V	
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.6	V
I _{DSS}	drain leakage current	V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C	-	0.1	1	μA
		V _{DS} = 120 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	4.7	6.72	7.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 13	-	19.4	22.9	mΩ

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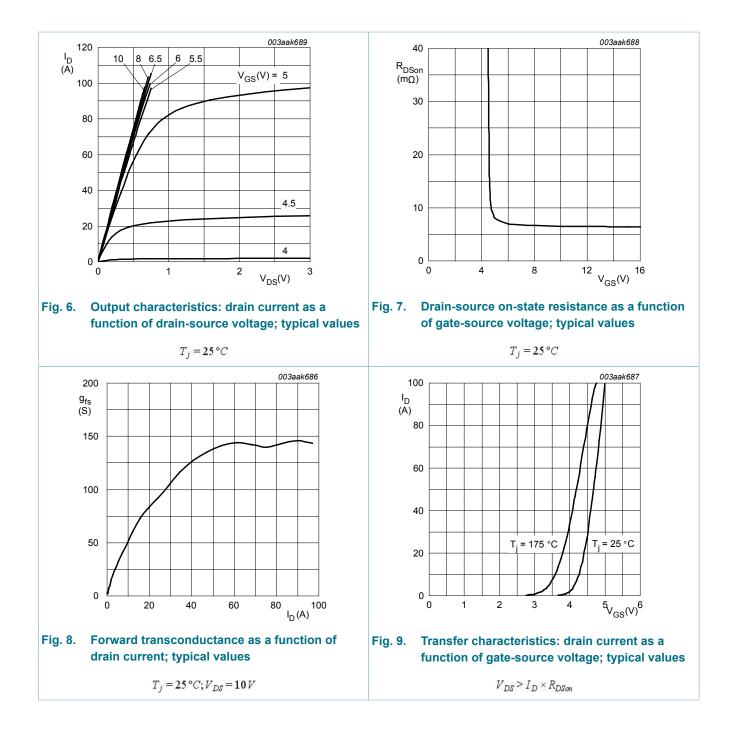
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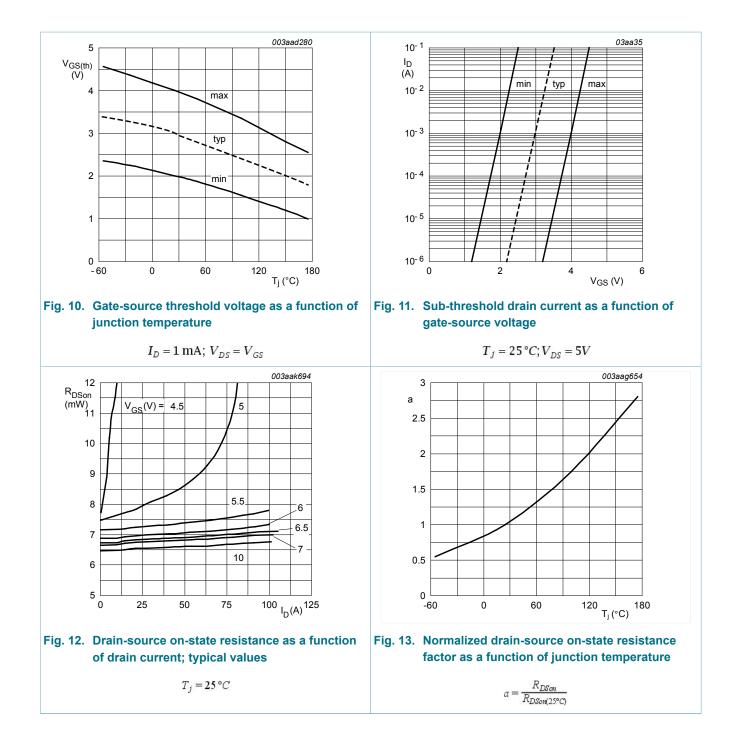
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _G	internal gate resistance (AC)	f = 1 MHz	0.39	0.78	1.56	Ω
Dynamic ch	naracteristics	· · · ·				
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V;	-	167	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15	-	36.9	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	24.2	-	nC
$Q_{GS(\text{th-pl})}$	post-threshold gate- source charge		-	12.7	-	nC
Q _{GD}	gate-drain charge	_	-	50.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 60 V; <u>Fig. 14; Fig. 15</u>	-	4.5	-	V
C _{iss}	input capacitance	V _{DS} = 60 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>	-	9473	-	pF
C _{oss}	output capacitance		-	441	-	pF
C _{rss}	reverse transfer capacitance		-	298	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V;	-	45.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	55.3	-	ns
t _{d(off)}	turn-off delay time	-	-	151.8	-	ns
t _f	fall time		-	60.8	-	ns
Source-drai	in diode	· · · · · · · · · · · · · · · · · · ·	1			
V _{SD}	source-drain voltage	$I_{\rm S}$ = 25 A; $V_{\rm GS}$ = 0 V; $T_{\rm j}$ = 25 °C; <u>Fig. 17</u>	-	0.81	1.2	V
t _{rr}	reverse recovery time	I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	75.7	-	ns
Qr	recovered charge	V _{DS} = 60 V	-	264	-	nC

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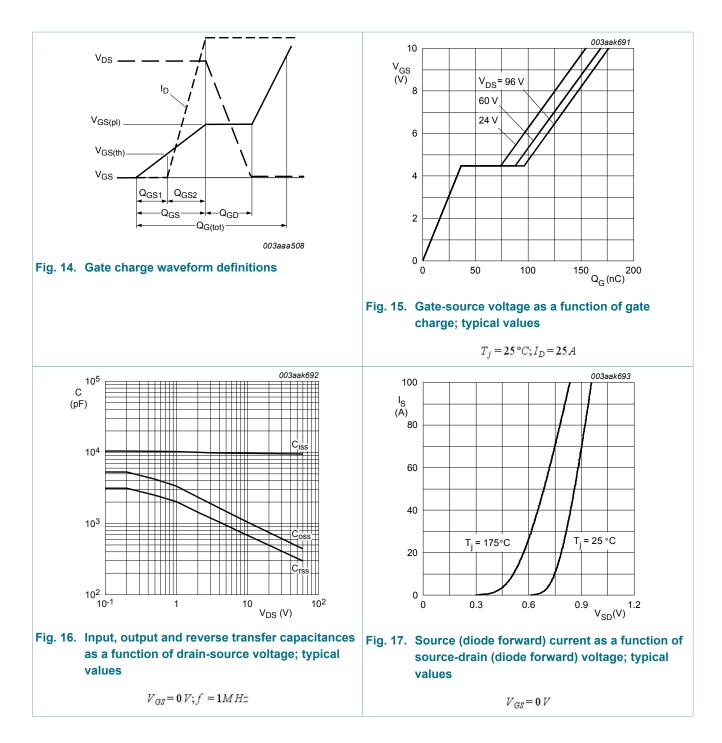
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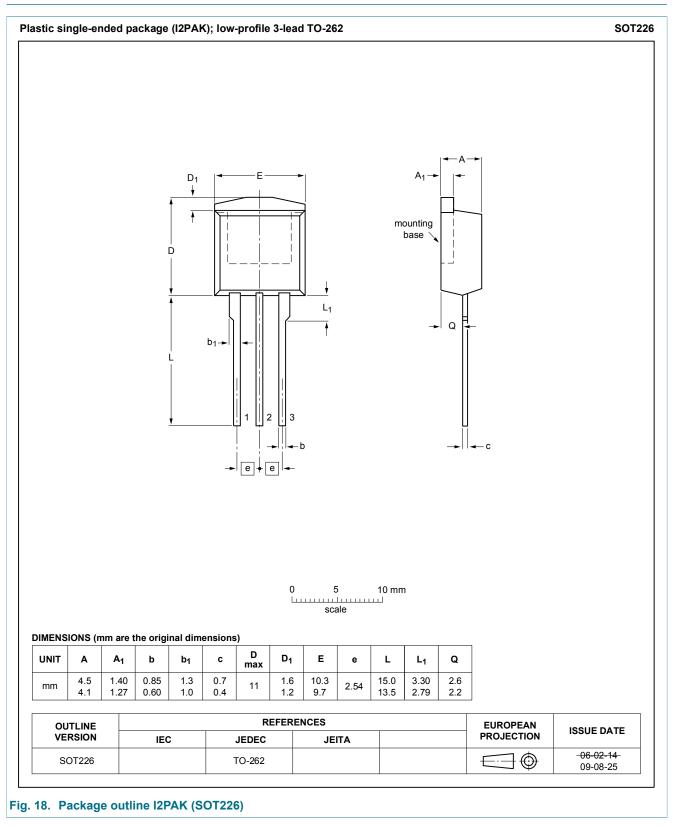
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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